

Nam-Hoon Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Variation of Surface Nanostructures on (100) PbS Single Crystals during Argon Plasma Treatment. Crystals, 2022, 12, 111.	2.2	2
2	Magnetron Sputter-Deposited In^{2+} -Ga ₂ O ₃ Films on c-Sapphire Substrate: Effect of Rapid Thermal Annealing Temperature on Crystalline Quality. Coatings, 2022, 12, 140.	2.6	7
3	Electronic Structure and Thermoelectric Properties of Mg ₂ Sn Films Fabricated by Using Co-Sputtering Process With Stoichiometric Modification. IEEE Access, 2022, 10, 380-390.	4.2	0
4	Hydrophobic Anti-Reflective Coating of Plasma-Enhanced Chemical Vapor Deposited Diamond-Like Carbon Thin Films with Various Thicknesses for Dye-Sensitized Solar Cells. Applied Sciences (Switzerland), 2021, 11, 358.	2.5	9
5	Modification of Nanocrystalline Porous Cu _{2-x} Se Films during Argon Plasma Treatment. Applied Sciences (Switzerland), 2021, 11, 612.	2.5	1
6	Impurity Phases and Optoelectronic Properties of CuSbSe ₂ Thin Films Prepared by Cosputtering Process for Absorber Layer in Solar Cells. Coatings, 2020, 10, 1209.	2.6	13
7	Optoelectronic properties of two-dimensional molybdenum diselenide dual-gated MISFET-based photodetector. Optik, 2020, 224, 165427.	2.9	3
8	Thickness Dependence of Optoelectronic Properties of Molybdenum Diselenide-Based Nanodevices. Journal of Electronic Materials, 2019, 48, 7025-7030.	2.2	5
9	TiC/a-C Nano-Composite Films Fabricated by Using Closed-Field Unbalanced Magnetron Sputtering for Biomedical Applications. Journal of the Korean Physical Society, 2019, 75, 380-384.	0.7	2
10	Micro-Hall Sensors Based on Two-Dimensional Molybdenum Diselenide. Journal of Nanoscience and Nanotechnology, 2019, 19, 4330-4332.	0.9	3
11	Dependence of Structural, Compositional, Electrical, and Optical Properties of Sputtering-Deposited CdS Thin Films on Laser-Annealing Power. Science of Advanced Materials, 2018, 10, 232-237.	0.7	1
12	Effects of Rapid Thermal Treatment on Characteristics of Magnetron-Sputtered NiO Thin Films for Supercapacitor Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 6213-6219.	0.9	7
13	Optoelectronic Characterizations of Two-Dimensional h-BN/MoSe ₂ Heterostructures Based Photodetector. Science of Advanced Materials, 2018, 10, 627-631.	0.7	6
14	Tribological and Electrical Properties of Chromium Doped Diamond-Like Carbon Films Deposited by Unbalanced Magnetron Sputtering. Science of Advanced Materials, 2018, 10, 429-432.	0.7	0
15	Electrical Characteristics of Metal-Insulator-Semiconductor Structure Using a-C:H Films Fabricated by Dual Magnetron Sputtering. Science of Advanced Materials, 2018, 10, 433-437.	0.7	0
16	High-performance near-infrared photodetector based on nano-layered MoSe ₂ . Semiconductor Science and Technology, 2017, 32, 065015.	2.0	46
17	Rapid laser annealing of Cu(In,Ga)Se ₂ thin films by using a continuous wave Nd:YAG laser ($\lambda = 532$ nm). Journal of the Korean Physical Society, 2017, 70, 809-815.	0.7	3
18	Cu(In,Ga)Se ₂ thin films annealed using a continuous wave Nd:YAG laser ($\lambda = 532$ nm): Effects of laser-annealing time. Journal of the Korean Physical Society, 2017, 71, 1038-1047.	0.7	2

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19	Gate-tunable optoelectronic properties of a nano-layered GaSe photodetector. <i>Optical Materials Express</i> , 2017, 7, 587.	3.0	18
20	Characteristics of InZnSnO Thin Films Deposited by Dual Magnetron Sputtering for Thin Films Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 7164-7168.	0.9	0
21	Deviations from stoichiometry and molecularity in non-stoichiometric Ag-In-Se thin films: Effects on the optical and the electrical properties. <i>Journal of the Korean Physical Society</i> , 2016, 69, 1817-1823.	0.7	1
22	Characteristics of SnO ₂ /Sb Films as Transparent Conductive Electrodes of Flexible Inverted Organic Solar Cells. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 4973-4977.	0.9	9
23	Amorphous Indium Selenide Thin Films Prepared by RF Sputtering: Thickness-Induced Characteristics. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 5128-5132.	0.9	1
24	Heavily-doped ZnO:Al thin films prepared by using magnetron Co-sputtering: Optical and electrical properties. <i>Journal of the Korean Physical Society</i> , 2016, 69, 220-225.	0.7	4
25	Thickness dependence on the optoelectronic properties of multilayered GaSe based photodetector. <i>Nanotechnology</i> , 2016, 27, 325202.	2.6	34
26	Non-Stoichiometric Amorphous Indium Selenide Thin Films as a Buffer Layer for CIGS Solar Cells with Various Temperatures in Rapid Thermal Annealing. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 5070-5073.	0.9	0
27	Characteristics of W Doped Nanocrystalline Carbon Films Prepared by Unbalanced Magnetron Sputtering. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 4989-4992.	0.9	0
28	Co-Sputtered and Rapid-Thermal-Annealed CIAS Thin Films Using CuSe ₂ /In/Al Triple Targets of Varying In/Al Compositions. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 1583-1586.	0.9	2
29	Hydrogenation in 808-nm Diode Laser Annealing of CdTe Thin Films: Structural, Optical, and Electrical Properties. <i>Science of Advanced Materials</i> , 2016, 8, 1813-1818.	0.7	3
30	Low-temperature, rapid thermal annealing of CIS thin films deposited by using a co-sputtering process with In and CuSe ₂ targets. <i>Journal of the Korean Physical Society</i> , 2015, 66, 1001-1008.	0.7	3
31	Optimized Digital Proportional Integral Derivative Controller for Heating and Cooling Injection Molding System. <i>Journal of Electrical Engineering and Technology</i> , 2015, 10, 1383-1388.	2.0	3
32	Se-loss-induced CIS Thin Films in RTA Process after Co-sputtering Using CuSe ₂ and InSe ₂ Targets. <i>Journal of Electrical Engineering and Technology</i> , 2014, 9, 1009-1015.	2.0	2
33	Microstructure, stress and optical properties of CdTe thin films laser-annealed by using an 808-nm diode laser: Effect of the laser scanning velocity. <i>Journal of the Korean Physical Society</i> , 2013, 63, 229-235.	0.7	17
34	A pilot investigation on laser annealing for thin-film solar cells: Crystallinity and optical properties of laser-annealed CdTe thin films by using an 808-nm diode laser. <i>Journal of the Korean Physical Society</i> , 2013, 62, 502-507.	0.7	15
35	AMORPHOUS COPPER DISELENIDE THIN FILMS DOPED WITH GALLIUM AND INDIUM BY LASER-INDUCED DOPING. <i>International Journal of Modern Physics B</i> , 2013, 27, 1350030.	2.0	2
36	Laser-Induced Indium-Diffusion into Cadmium Sulfide Thin Film for Solar Cell Applications. <i>Chinese Physics Letters</i> , 2012, 29, 127302.	3.3	2

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37	Electrical and optical properties of sputter-deposited cadmium sulfide thin films optimized by annealing temperature. <i>Materials Science in Semiconductor Processing</i> , 2012, 15, 125-130.	4.0	33
38	Non-selenization method using sputtering deposition with a CuSe ₂ target for CIGS thin film. <i>Journal of the Korean Physical Society</i> , 2012, 61, 1177-1180.	0.7	13
39	Laser-induced doping of aluminum into a cadmium telluride thin film: Electrical and optical properties. <i>Journal of the Korean Physical Society</i> , 2012, 60, 425-429.	0.7	8
40	Universal Surface Hydrophilicity Obtained by Using Low-temperature Plasma H ₂ O gas for Nanosphere Lithography. <i>Journal of the Korean Physical Society</i> , 2011, 58, 1-4.	0.7	7
41	Effective Ag Doping by He-Ne Laser Exposure to Improve the Electrical and the Optical Properties of CdTe Thin Films for Heterostructured Thin Film Solar Cells. <i>Journal of the Korean Physical Society</i> , 2011, 59, 2286-2290.	0.7	8
42	Improvement of the Sensitivity for Silica Humidity Sensors with a Multiple-layered Silica Bead Coating. <i>Journal of the Korean Physical Society</i> , 2011, 59, 3325-3328.	0.7	0
43	Electrical Characteristics and Doping Mechanism of DNA Molecules Doped with Iodine Solutions. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 3484-3488.	0.9	1
44	Influences of thickness-uniformity and surface morphology on the electrical and optical properties of sputtered CdTe thin films for large-area II-VI semiconductor heterostructured solar cells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 171, 73-78.	3.5	36
45	Stabilization of sheet resistance for metal lines by formation of etch stop layer (ESL) trench structure. <i>Microelectronic Engineering</i> , 2010, 87, 343-347.	2.4	3
46	Enhancement of optical properties for CdTe absorber through improving thickness uniformity by CMP process. <i>Electronics Letters</i> , 2010, 46, 1019.	1.0	1
47	Fabrication of Highly Uniform Conductive Polypyrrole Nanowires with DNA Template. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 3180-3184.	0.9	9
48	Fabrication of Si-based two-dimensional photonic quasicrystals by using multiple-exposure holographic lithography. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 1886.	1.3	12
49	Reduction of loading effects with the sufficient vertical profile for deep trench silicon etching by using decoupled plasma sources. <i>Journal of Materials Processing Technology</i> , 2009, 209, 5818-5829.	6.3	9
50	Fabrication of SiO ₂ nano-dots by block copolymer lithography and liquid phase deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 147, 209-212.	3.5	11
51	Characteristics of gold nanowires and UV spectral changes by interaction between gold nanoparticles and DNA. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 2545-2550.	2.7	2
52	Performance and characteristics of imprint mould fabricated by liquid-phase deposition. <i>Superlattices and Microstructures</i> , 2008, 44, 520-527.	3.1	3
53	Polishing damages to electrical properties of BLT thin film capacitors fabricated by damascene process of chemical mechanical polishing. , 2008, , .		0
54	Polishing damages to electrical properties of BLT thin-film capacitors fabricated by damascene process. <i>Electronics Letters</i> , 2008, 44, 1429.	1.0	1

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55	Influence of a post-chemical mechanical polishing cleaning process on the ferroelectric properties of a Pb(Zr,Ti)O ₃ thin film capacitor fabricated by the damascene process. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 720-723.	2.1	1
56	Improvement of the surface roughness and sensing properties of cerium dioxide thin film by chemical mechanical polishing. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 794-797.	2.1	7
57	Nanometer-scaled triangular platinum islands fabricated using the bridge phenomenon of polystyrene beads. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008, 26, 819-823.	2.1	4
58	Yield improvement of 0.13- μ m Cu/low-k dual-damascene interconnection by organic cleaning process. <i>Journal of Vacuum Science & Technology B</i> , 2007, 25, 1819.	1.3	3
59	Electrical and Thermal Properties of Platinum Thin Films Prepared by DC Magnetron Sputtering for Micro-Heater of Microsensor Applications after CMP Process. <i>Solid State Phenomena</i> , 2007, 124-126, 267-270.	0.3	17
60	Indium Tin Oxide Film Characteristics after Chemical Mechanical Polishing Process with Control of Pad Conditioning Temperature. <i>Solid State Phenomena</i> , 2007, 124-126, 263-266.	0.3	0
61	Chemical mechanical polishing characteristics in (Bi,Lu)Ti ₃ O ₁₂ damascene process for high-density ferroelectric memories. <i>Thin Solid Films</i> , 2007, 515, 6456-6459.	1.8	7
62	Platinum chemical mechanical polishing (CMP) characteristics for high density ferroelectric memory applications. <i>Microelectronic Engineering</i> , 2007, 84, 2702-2706.	2.4	6
63	Creation mechanism of metal depression in sputtering process for aluminum interconnects. <i>Microelectronic Engineering</i> , 2007, 84, 2471-2475.	2.4	1
64	Electromigration characteristics in dual-damascene copper interconnects by difference of via structures. <i>Microelectronic Engineering</i> , 2007, 84, 2663-2668.	2.4	8
65	Periodic Nanometer-Scale Holes Fabricated by Using Plasma Ashing Technique and Selective Liquid Phase Deposition. <i>Journal of the Korean Physical Society</i> , 2007, 51, 234.	0.7	1
66	Improvement of TEOS-chemical mechanical polishing performance by control of slurry temperature. <i>Microelectronic Engineering</i> , 2006, 83, 286-292.	2.4	16
67	Temperature effects of pad conditioning process on oxide CMP: Polishing pad, slurry characteristics, and surface reactions. <i>Microelectronic Engineering</i> , 2006, 83, 362-370.	2.4	52
68	CMP characteristics and optical property of ITO thin film by using silica slurry with a variety of process parameters. <i>Microelectronic Engineering</i> , 2006, 83, 2213-2217.	2.4	19
69	Electrochemical corrosion effects and chemical mechanical polishing characteristics of tungsten film using mixed oxidizers. <i>Microelectronic Engineering</i> , 2006, 83, 428-433.	2.4	8
70	Design of experiment (DOE) method considering interaction effect of process parameters for optimization of copper chemical mechanical polishing (CMP) process. <i>Microelectronic Engineering</i> , 2006, 83, 506-512.	2.4	34
71	Chemical mechanical polishing (CMP) mechanisms of thermal SiO ₂ film after high-temperature pad conditioning. <i>Thin Solid Films</i> , 2006, 504, 166-169.	1.8	21
72	Chemical mechanical polishing of BTO thin film for vertical sidewall patterning of high-density memory capacitor. <i>Thin Solid Films</i> , 2006, 504, 261-264.	1.8	8

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73	Chemical mechanical polishing and electrochemical characteristics of tungsten using mixed oxidizers with hydrogen peroxide and ferric nitrate. <i>Materials Letters</i> , 2006, 60, 1192-1197.	2.6	30
74	Behaviour of electrical and optical properties of indium tin oxide transparent electrode after CMP process. <i>Electronics Letters</i> , 2006, 42, 487.	1.0	11
75	Effects of various oxidizers on chemical mechanical polishing performance of nickel for microelectromechanical system applications. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 1297-1301.	2.1	12
76	Chemical mechanical polishing performances by filtering and retreatment of used silica abrasives slurry. <i>Microelectronic Engineering</i> , 2005, 77, 358-364.	2.4	12
77	Optimization of nitride films for linear pre-metal dielectric process. <i>Microelectronic Engineering</i> , 2005, 81, 29-34.	2.4	1
78	Agglomeration characteristic of particles in alumina slurry by addition of chemicals and milling process for Cu CMP. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 118, 306-309.	3.5	7
79	Effect of nonionic surfactants on the stability of alumina slurry for Cu CMP. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 118, 293-300.	3.5	15
80	Structural and surface properties of NiCr thin films prepared by DC magnetron sputtering under variation of annealing conditions. <i>Microelectronic Engineering</i> , 2005, 82, 314-320.	2.4	36
81	Effects of conditioning temperature on polishing pad for oxide chemical mechanical polishing process. <i>Microelectronic Engineering</i> , 2005, 82, 680-685.	2.4	6
82	Semi-abrasive free slurry with acid colloidal silica for copper chemical mechanical planarization. <i>Journal of Materials Science: Materials in Electronics</i> , 2005, 16, 629-632.	2.2	7
83	Surface and sensing properties of PE-ALD SnO ₂ thin film. <i>Electronics Letters</i> , 2005, 41, 475.	1.0	9
84	Effects of Silica Slurry Temperature on Chemical Mechanical Polishing for Tetraethyl Orthosilicate Film. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1256-L1258.	1.5	8
85	Removal characteristics of hillock on SnO ₂ thin film by chemical mechanical polishing process. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 1133-1136.	2.1	15
86	Chemical mechanical planarization characteristics of WO ₃ thin film for gas sensing. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2005, 23, 737-740.	2.1	9
87	Improvement of resistance characteristics of NiCr thin film by gradational double annealing process. <i>Electronics Letters</i> , 2005, 41, 982.	1.0	2
88	Electrochemical Patterning of Copper Using Microcontact Printing. <i>Journal of the Electrochemical Society</i> , 2004, 151, C455.	2.9	4
89	Recycling method for used slurry by annealed filtering. <i>Electronics Letters</i> , 2004, 40, 1553.	1.0	2
90	Acid colloidal silica slurry for Cu CMP. <i>Electronics Letters</i> , 2004, 40, 26.	1.0	0

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91	Isothermal aging characteristics of Sn-Pb micro solder bumps. Microelectronics Reliability, 2003, 43, 757-763.	1.7	37
92	Effects of phosphoric acid stabilizer on copper and tantalum nitride CMP. Materials Letters, 2003, 57, 4601-4604.	2.6	23
93	H3PO4 addition to slurry for Cu and TaN CMP. Electronics Letters, 2003, 39, 718.	1.0	6
94	Aging Treatment Characteristics of Shear Strength in Micro Solder Bump. Materials Transactions, 2002, 43, 3234-3238.	1.2	4
95	Roles of N2 gas in etching of platinum by inductively coupled Ar/Cl2/N2 plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1377-1380.	2.1	4
96	Defects controlled stress engineering in Al-doped ZnO transparent multilayered thin films. Journal of the Korean Ceramic Society, 0, , .	2.3	2